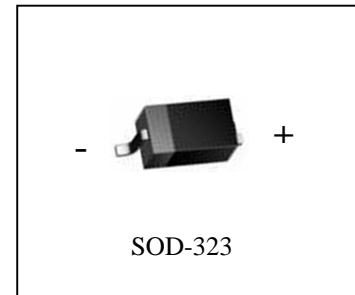


SCHOTTKY BARRIER DIODE
B5817WS/B5818WS/B5819WS
FEATURES

or use in low voltage, high frequency inverters
 Free wheeling, and polarity protection applications.

MARKING : B5817WS: SJ B5818WS:SK B5819WS: SL



Maximum Ratings and Electrical Characteristics, Single Diode @TA=25 °C

Parameter	Symbol	B5817WS	B5818WS	B5819WS	Unit
Non-Repetitive Peak reverse voltage	V _{RM}	20	30	40	V
Peak repetitive Peak reverse voltage	V _{RRM}	20	30	40	V
Working Peak Reverse Voltage	V _{VRWM}				
DC Blocking Voltage	V _R	14	21	28	V
RMS Reverse Voltage	V _{R(RMS)}				
Average Rectified Output Current	I _O	1			A
Peak forward surge current @=8.3ms	I _{FSM}	9			A
Repetitive Peak Forward Current	I _{FR}	1.5			A
Power Dissipation	P _d	250			mW
ThermalResistanc Junction to Ambient	R _{JA}	500			°C/W
Storage temperature	T _{STG}	-65~+150			°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Max	Unit
		IR= 1mA	B5817WS B5818WS B5819WS			
Reverse breakdown voltage	V _(BR)	IR= 1mA	B5817WS B5818WS B5819WS	20 30 40		V
Reverse voltage leakage current	I _R	VR=20V VR=30V VR=40V	B5817WS B5818WS B5819WS		1	mA
Forward voltage	V _F	IF=1A IF=3A	B5817WS		0.45 0.75	V
			B5818WS		0.55 0.875	V
			B5819WS		0.6 0.9	V
Diode capacitance	C	VR=4V, f=1MHz			120	pF

B5817WS/B5818WS/B5819WS

Typical Characteristics

Fig. 1 - Forward Current Derating Curve

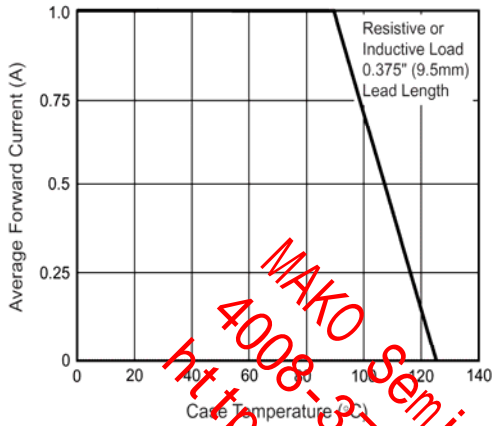


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current

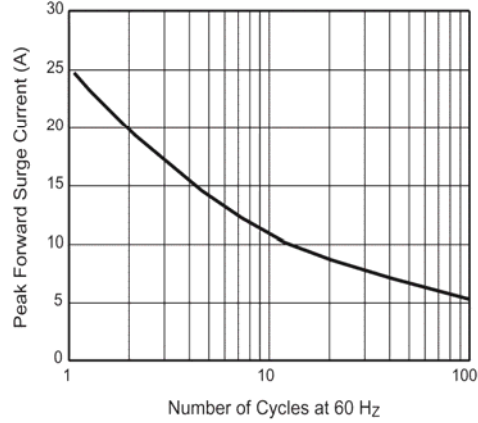


Fig. 3 - Typical Instantaneous Forward Characteristics

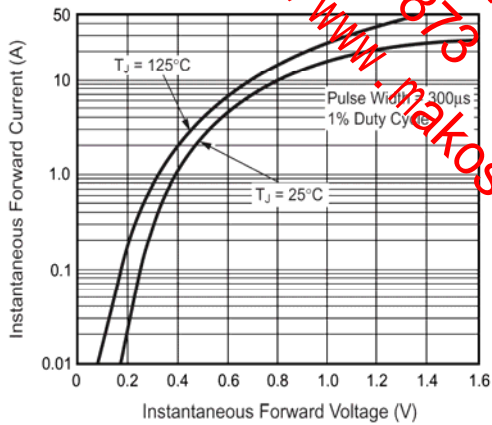


Fig. 4 - Typical Reverse Characteristics

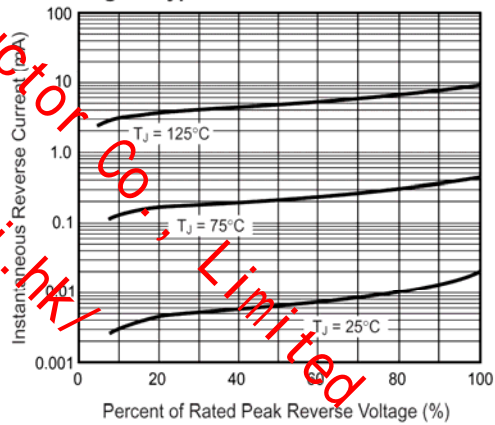


Fig. 5 - Typical Junction Capacitance

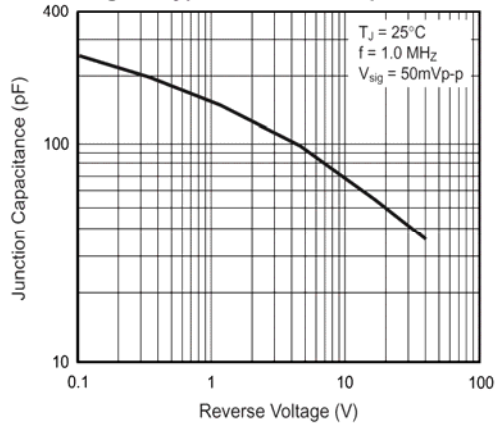


Fig. 6 - Typical Transient Thermal Impedance

